Supporting Information

Atomic Scale Surface Modification of TiO_2 3D Nano-Arrays: Plasma Enhanced Atomic Layer Deposition of NiO for Photocatalysis

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Figure S1: A 20 nm NiO film grown onto an 8" Si wafer with a 100 nm thermal oxide layer wafer at 250 °C using the 2 s/5 s/2 s/5 s optimised pulse sequence



Figure S2: XRD patterns of NiO PEALD samples grown between 100-300 $^{\circ}\mathrm{C}$ onto SiO₂ using the $2\,\mathrm{s}/5\,\mathrm{s}/2\,\mathrm{s}/5\,\mathrm{s}$ optimised pulse sequence



Figure S3: XPS measurements and analysis of a 100 nm NiO sample deposited at 250 $^{\circ}\rm C$ onto SiO₂ using the $2\,\rm s/5\,\rm s/2\,\rm s/5\,\rm s$ optimised pulse sequence



Figure S4: Tauc plot calculated from reflection and refracion data of a 20 nm NiO sample grown onto borosilicate glass, with an estimated bandgap of 3.62 eV.



Figure S5: ToF-ERDA measurements of a 100 nm NiO sample grown by Ni(Cp)₂ PEALD onto SiO₂ at 250 °C with 100 W RF pulses and the 2s/5s/2s/5s optimised pulse sequence



Figure S6: SEM-EDX imaging analysis of TiO₂nanorods coated with 600 NiO PEALD cycles deposited at 250 °C(a) A control section of FTO masked during NiO deposition(b) and (C) SEM-EDX of NiO coated TiO₂NTs



Figure S7: SEM imaging of a 100 nm NiO film grown at 250 °C onto SiO₂ using the 2 s/5 s/2 s/5 s optimised pulse sequence